

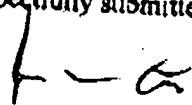
implant may be performed to extend source/drain regions 34 over the bottom portion of source/drain pockets 32. Either one of these well-known methods reduces the capacitance of the transistor, thereby improving transistor performance."

REMARKS

The confusion caused by the last requested amendment to the specification is regretted and understood. To overcome the problem, the above new paragraph to the specification is identical to the wording of that paragraph in the reply file November 5, 2001 with all underline and brackets removed therefrom. Accordingly, all objected to language has now been removed. In the event there remains a problem with the wording, the Examiner is requested to call the undersigned at 301-424-0355 at his home.

In view of the above remarks, favorable reconsideration and allowance are respectfully requested.

Respectfully submitted,



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GH MBH Referring to FIGURE 1E, source/drain regions 34 are formed around source/drain pockets 32 using ion implantation. In this example, source/drain regions 34 are implanted with an n-type material such as arsenic.. Although source/drain pockets 32 are shown extending around and within source/drain regions 34 and adjoining isolation trenches 20, it will be understood that source/drain pockets 32 may extend only along the inside portion of source/drain regions 34, the latter adjoining the channel region 24. Alternatively, a deeper source/drain implant may be performed to extend source/drain regions 34 over the bottom portion of source/drain pockets 32. Either one of these well-known methods reduces the capacitance of the transistor, thereby improving transistor performance.